3 A Dual High-Speed MOSFET Drivers

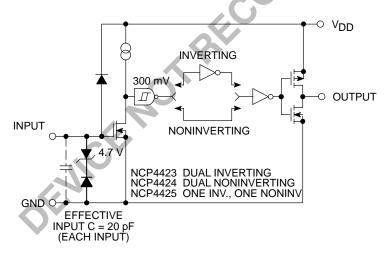
The NCP4423/4424/4425 are MOSFET drivers that are capable of giving reliable service in demanding electrical environments.

Although primarily intended for driving power MOSFETs, these drivers are well–suited for driving other loads (capacitive, resistive, or inductive) which require a low impedance driver capable of high peak currents and fast switching times. Applications such as heavily loaded clock lines, coaxial cables, or piezoelectric transducers can all be driven with the NCP4423/4424/4425. The only known limitation on loading is that the total power dissipated of the driver must be kept within the maximum power dissipation limits of the package.

Features

- High Peak Output Current (3 A)
- Wide Operating Range (4.5 V to 18 V)
- High Capacitive Load Drive Capability (1800 pF in 25 nsec)
- Short Delay Times (<40 nsec Typ)
- Matched Rise/Fall Times
- Low Supply Current
 With Logic "1" Input (3.5 mA)
 With Logic "0" Input (350 μA)
- Low Output Impedance (3.5 Ω Typ)
- Latch-Up Protected: Will Withstand 1.5 A Reverse Current
- Logic Input Will Withstand Negative Swing Up to 5 V
- ESD Protected (4 kV)

FUNCTIONAL BLOCK DIAGRAM



NOTES

- 1. NCP4425 has one inverting and one noninverting driver.
- 2. Ground any unused driver input.



http://onsemi.com





SO-16 DW SUFFIX CASE 751G





PDIP-8 P SUFFIX CASE 626



x = Device Number (3, 4, or 5)

YY = Year

WW = Work Week

X = Assembly ID Code

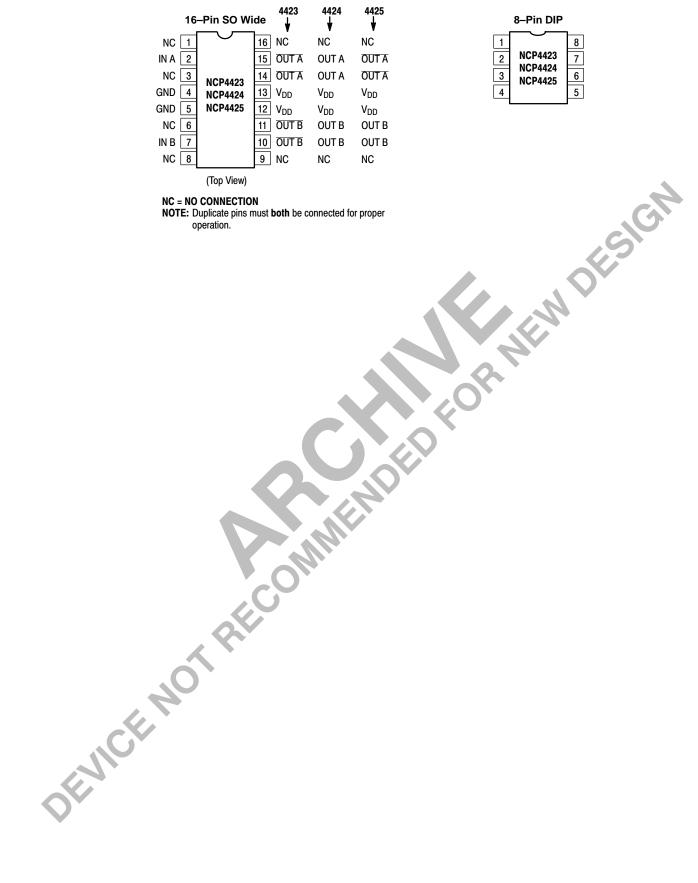
Z = Subcontractor ID Code

CO = Country of Origin

ORDERING INFORMATION

| Device | Package | Shipping | |
|-------------|---------|------------------|--|
| NCP4423DWR2 | SO-16 | 1000 Tape & Reel | |
| NCP4424DWR2 | SO-16 | 1000 Tape & Reel | |
| NCP4425DWR2 | SO-16 | 1000 Tape & Reel | |
| NCP4423P | PDIP-8 | 50 Units/Rail | |
| NCP4424P | PDIP-8 | 50 Units/Rail | |
| NCP4425P | PDIP-8 | 50 Units/Rail | |

PIN CONNECTIONS



ABSOLUTE MAXIMUM RATINGS

| Rating | Value | Unit |
|--|--------------------|----------|
| Supply Voltage | +22 | V |
| Input Voltage, IN A or IN B (V _{DD} + 0.3 V to GND – 5.0 V) | -5 | V |
| Maximum Chip Temperature | +150 | °C |
| Storage Temperature Range, T _{stg} | -65 to +150 | °C |
| Lead Temperature (Soldering, 10 sec) | +300 | °C |
| Package Thermal Resistance SOIC, $R_{\theta JA}$ PDIP, $R_{\theta JC}$ | 155 –125 –45 | °C/W |
| Operating Temperature Range | -40 to +85 | °C |
| Package Power Dissipation ($T_A \le 70^{\circ}C$) SOIC PDIP | 470 730 | mW mc |

ELECTRICAL CHARACTERISTICS (T_A = +25°C with 4.5 V \leq V_{DD} \leq 18 V, unless otherwise specified.)

| Characteristic | Symbol | Test Conditions | Min | Тур | Max | Unit |
|--|------------------|--|------------------------|-------------|-------------|------|
| Input | | | | | | |
| Logic 1 High Input Voltage | V _{OH} | - | 2.4 | 17. | - | V |
| Logic 0 Low Input Voltage | V _{IL} | - | - 1 | / - | 0.8 | V |
| Input Current | I _{IN} | $0 \text{ V} \leq \text{V}_{IN} \leq \text{V}_{DD}$ | -1.0 | _ | 1.0 | μΑ |
| Output | | | | | | |
| High Output Voltage | V _{OH} | - | V _{DD} -0.025 | _ | - | V |
| Low Output Voltage | V _{OL} | - \ | - | _ | 0.025 | V |
| Output Resistance, High | R _{OH} | I _{OUT} = 10 mA, V _{DD} = 18 V | _ | 2.8 | 5.0 | Ω |
| Output Resistance, Low | R _{OL} | I _{OUT} = 10 mA, V _{DD} = 18 V | _ | 3.5 | 5.0 | Ω |
| Peak Output Current | I _{PK} | _ | - | 3.0 | - | Α |
| Latch–Up Protection Withstand Reverse Current | I _{REV} | Duty Cycle ≤ 2% t ≤ 300 μs | 1.5 | - | _ | А |
| Switching Time (Note 1) | | | | | | |
| Rise Time | t _R | Figure 1, C _L = 1800 pF | _ | 23 | 35 | nsec |
| Fall Time | t _F | Figure 1, C _L = 1800 pF | - | 25 | 35 | nsec |
| Delay Time 1 | t _{D1} | Figure 1, C _L = 1800 pF | - | 33 | 75 | nsec |
| Delay Time 2 | t _{D2} | Figure 1, C _L = 1800 pF | _ | 38 | 75 | nsec |
| Power Supply | | | | | | |
| Power Supply Current | I _S | V _{IN} = 3.0 V (Both Inputs) V _{IN} = 0 V (Both Inputs) | _ | 1.5 0.15 | 2.5 0.25 | mA |

^{1.} Switching times guaranteed by design.

ELECTRICAL CHARACTERISTICS (Over operating temperature range with 4.5 V \leq V_{DD} \leq 18 V, unless otherwise specified.)

| Characteristic | Symbol | Test Conditions | Min | Тур | Max | Unit |
|--|------------------|--|------------------------|------------|------------|------|
| Input | | | | | | |
| Logic 1 High Input Voltage | V _{IH} | _ | 2.4 | - | _ | V |
| Logic 0 Low Input Voltage | V _{IL} | _ | - | - | 0.8 | V |
| Input Current | I _{IN} | $0 \text{ V} \leq \text{V}_{\text{IN}} \leq \text{V}_{\text{DD}}$ | -10 | - | 10 | μΑ |
| Output | | | | | | |
| High Output Voltage | V _{OH} | _ | V _{DD} -0.025 | - | _ | V |
| Low Output Voltage | V _{OL} | _ | _ | - | 0.025 | V |
| Output Resistance, High | R _O | I _{OUT} = 10 mA, V _{DD} = 18 V | - | 3.7 | 8.0 | Ω |
| Output Resistance, Low | R _O | I _{OUT} = 10 mA, V _{DD} = 18 V | - | 4.3 | 8.0 | Ω |
| Peak Output Current | I _{PK} | - | - | 3.0 | | Α |
| Latch–Up Protection Withstand Reverse Current | I _{REV} | Duty Cycle ≤ 2% t ≤ 300 μsec | 1.5 | - | | А |
| Switching Time (Note 1) | | | | |) | |
| Rise Time | t _R | Figure 1, C _L = 1800 pF | V- ^ | 28 | 60 | nsec |
| Fall Time | t _F | Figure 1, C _L = 1800 pF | 4 | 32 | 60 | nsec |
| Delay Time 1 | t _{D1} | Figure 1, C _L = 1800 pF | Y- (3) | 32 | 100 | nsec |
| Delay Time 2 | t _{D2} | Figure 1, C _L = 1800 pF | | 38 | 100 | nsec |
| Power Supply | | | | | • | • |
| Power Supply Current | I _S | V _{IN} = 3.0 V (Both Inputs) V _{IN} = 0 V (Both Inputs) | - | 2.0 0.2 | 3.5 0.3 | mA |

^{1.} Switching times guaranteed by design.

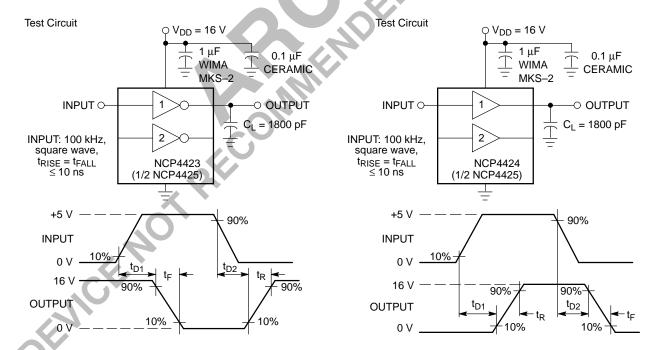
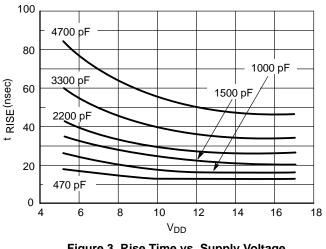


Figure 1. Inverting Driver Switching Time

Figure 2. Noninverting Driver Switching Time

TYPICAL ELECTRICAL CHARACTERISTICS



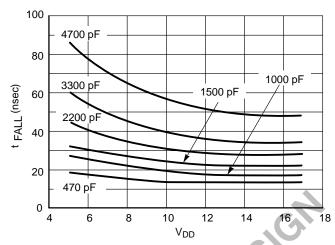
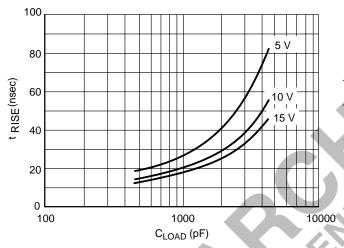


Figure 3. Rise Time vs. Supply Voltage

Figure 4. Fall Time vs. Supply Voltage



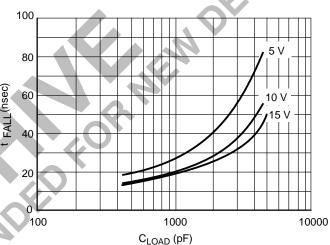
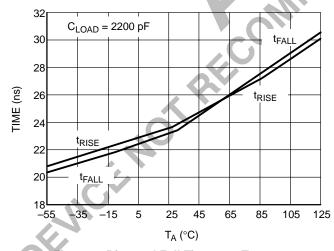


Figure 5. Rise Time vs. Capacitive Load

Figure 6. Fall Time vs. Capacitive Load



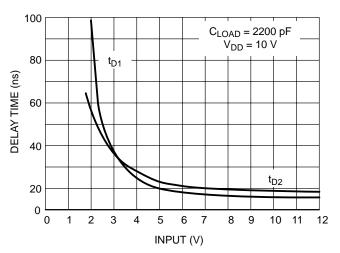


Figure 7. Rise and Fall Times vs. Temperature

Figure 8. Propagation Delay vs. Input Amplitude

TYPICAL ELECTRICAL CHARACTERISTICS

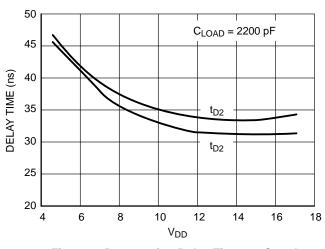


Figure 9. Propagation Delay Time vs. Supply Voltage

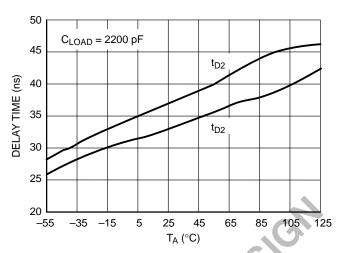


Figure 10. Delay Time vs. Temperature

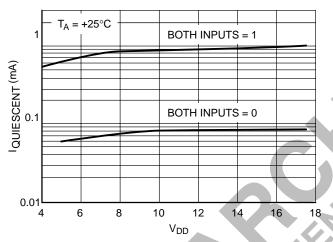


Figure 11. Quiescent Current vs. Supply Voltage

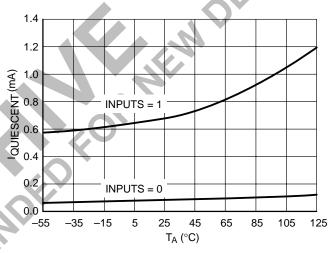


Figure 12. Quiescent Current vs. Temperature

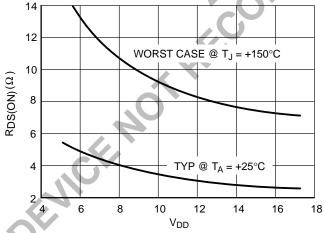


Figure 13. Output Resistance (Output High) vs. Supply Voltage

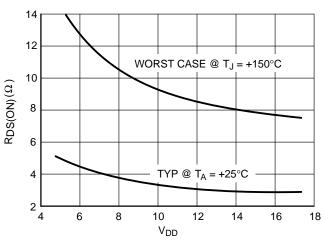
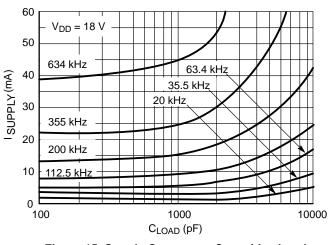


Figure 14. Output Resistance (Output Low) vs. Supply Voltage

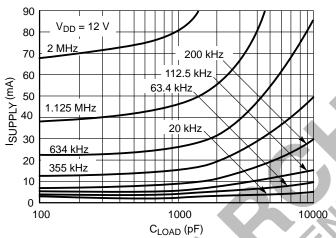
TYPICAL ELECTRICAL CHARACTERISTICS



60 3300 pF V_{DD} = 18 V 50 1000 pF 40 SUPPLY (mA) 30 10,000 pF 20 100 pF 10 0 10 100 FREQUENCY (kHz)

Figure 15. Supply Current vs. Capacitive Load

Figure 16. Supply Current vs. Frequency



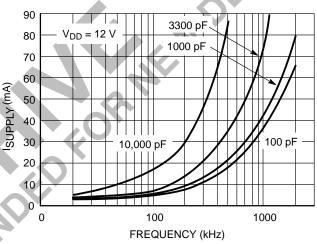
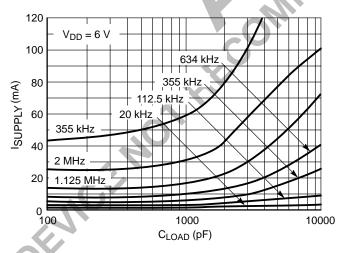


Figure 17. Supply Current vs. Capacitive Load

Figure 18. Supply Current vs. Frequency



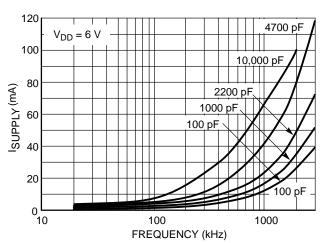
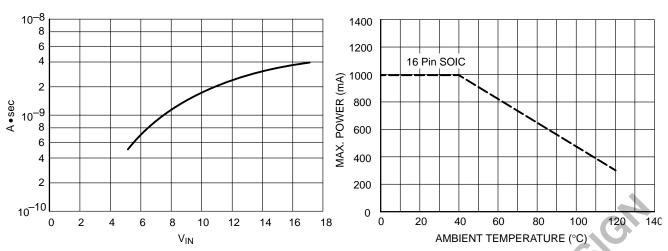


Figure 19. Supply Current vs. Capacitive Load

Figure 20. Supply Current vs. Frequency

TYPICAL ELECTRICAL CHARACTERISTICS

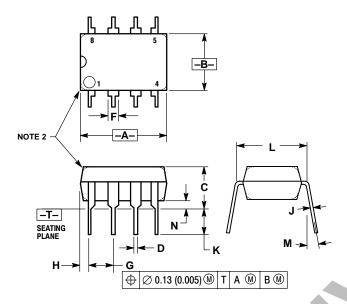


and a second sec

Figure 22. Thermal Derating Curves

PACKAGE DIMENSIONS

PDIP-8 **P SUFFIX** CASE 626-05 ISSUE K

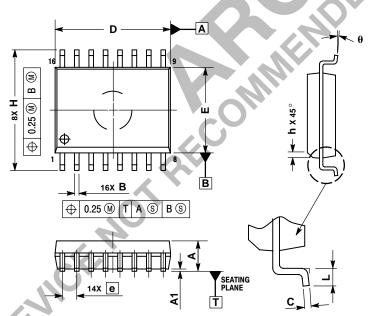


- NOTES:
 1. DIMENSION L TO CENTER OF LEAD WHEN
- FORMED PARALLEL.
 2. PACKAGE CONTOUR OPTIONAL (ROUND OR
- SQUARE CORNERS).

 3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

| | MILLIMETERS | | INCHES | |
|-----|-------------|-------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 9.40 | 10.16 | 0.370 | 0.400 |
| В | 6.10 | 6.60 | 0.240 | 0.260 |
| С | 3.94 | 4.45 | 0.155 | 0.175 |
| D | 0.38 | 0.51 | 0.015 | 0.020 |
| F | 1.02 | 1.78 | 0.040 | 0.070 |
| G | 2.54 | BSC | 0.100 BSC | |
| Н | 0.76 | 1.27 | 0.030 | 0.050 |
| J | 0.20 | 0.30 | 0.008 | 0.012 |
| K | 2.92 | 3.43 | 0.115 | 0.135 |
| L | 7.62 | BSC | 0.300 | BSC |
| M | | 10° | | → 10° |
| N | 0.76 | 1.01 | 0.030 | 0.040 |
| | | 1 | V | |
| | | 12 | | |

SO-16 DW SUFFIX CASE 751G-03 ISSUE B



NOTES:

- IOLES:

 1. DIMENSIONS ARE IN MILLIMETERS.

 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.

 3. DIMENSIONS D AND E DO NOT INLCUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

| | MILLIMETERS | | | | |
|-----|-------------|-------|--|--|--|
| DIM | MIN | MAX | | | |
| Α | 2.35 | 2.65 | | | |
| A1 | 0.10 | 0.25 | | | |
| В | 0.35 | 0.49 | | | |
| С | 0.23 | 0.32 | | | |
| D | 10.15 | 10.45 | | | |
| E | 7.40 | 7.60 | | | |
| е | 1.27 BSC | | | | |
| Н | 10.05 | 10.55 | | | |
| h | 0.25 | 0.75 | | | |
| L | 0.50 | 0.90 | | | |
| θ | 0 ° | 7° | | | |

Notes



Notes





ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax:** 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051

Phone: 81–3–5773–3850 Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local

Sales Representative.